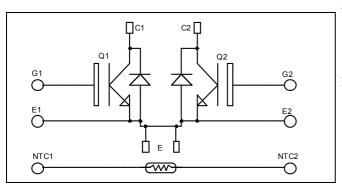


# Dual common source Fast Trench + Field Stop IGBT3 Power Module

$$V_{CES} = 1200V$$
  
 $I_C = 150A$  @  $Tc = 80$ °C

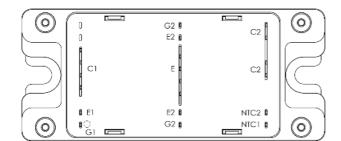


#### **Application**

- AC Switches
- Switched Mode Power Supplies
- Uninterruptible Power Supplies

#### **Features**

- Fast Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



#### **Benefits**

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

#### **Absolute maximum ratings**

Symbol	Parameter		Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage		1200	V
$I_{\mathrm{C}}$	Continuous Collector Current	$T_C = 25^{\circ}C$	220	
1C	Continuous Conector Current	$T_C = 80$ °C	150	A
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	350	
$V_{GE}$	Gate – Emitter Voltage		±20	V
$P_{D}$	Maximum Power Dissipation	$T_C = 25$ °C	690	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^{\circ}C$	300A @ 1150V	

These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



## All ratings @ $T_j = 25^{\circ}C$ unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$				250	μΑ
V	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25$ °C		1.7	2.1	V
$V_{CE(sat)}$		$I_C = 150A$ $T_j = 125^{\circ}C$	$T_j = 125$ °C		2.0		V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 3 \text{ mA}$		5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$				400	nA

**Dynamic Characteristics** 

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$		10.7		
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		0.56		nF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1MHz		0.48		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)		280		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		40		ns
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		420		
$T_{\mathrm{f}}$	Fall Time	$R_G = 2.2\Omega$		75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C	)	290		
$T_{r}$	Rise Time	$V_{GE} = \pm 15V$		45		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 150A$		520		ns
$T_{\rm f}$	Fall Time	$R_G = 2.2\Omega$		90		
Eon	Turn-on Switching Energy	$V_{GE} = \pm 15V \ V_{Bus} = 600V$ $T_j = 125^{\circ}C$		14		mJ
$E_{\text{off}}$	Turn-off Switching Energy	$I_C = 150A$ $R_G = 2.2\Omega$ $T_j = 125^{\circ}C$		16		111,7

Reverse diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage			1200			V
$I_{RM}$	Maximum Reverse Leakage Current	$V_{R}=1200V$	$T_j = 25^{\circ}C$			250	μА
1KM	Waximum Reverse Bearage Carrent	· K 1200 ·	$T_j = 125$ °C			500	μΛ
$I_{\mathrm{F}}$	DC Forward Current		$Tc = 80^{\circ}C$		150		A
$V_{\mathrm{F}}$	Diode Forward Voltage	$I_{\rm F} = 150A$	$T_i = 25^{\circ}C$		1.6	2.1	V
<b>*</b> F	Blode I of ward Voltage	1 <sub>F</sub> 13071	$T_{i} = 125^{\circ}C$		1.6		•
t <sub>rr</sub>	Reverse Recovery Time	ecovery Time $ T_j = 25^{\circ}C $ $ T_i = 125^{\circ}C $	$T_j = 25$ °C		170		ns
٩rr	reverse recovery Time		$T_j = 125$ °C		280		115
0	Reverse Recovery Charge	$I_F = 150A$ $V_R = 600V$	$T_j = 25^{\circ}C$		15		μС
$Q_{rr}$	Reverse Recovery Charge	$di/dt = 3000A/\mu s$	$T_{j} = 125^{\circ}C$		29		μС
$E_{r}$	Reverse Recovery Energy		$T_i = 25^{\circ}C$		7		mJ
$\mathbf{L}_{\mathrm{r}}$	Reverse Recovery Ellergy		$T_j = 125$ °C		12		1113



 $Temperature\ sensor\ NTC\ (see\ application\ note\ APT0406\ on\ www.microsemi.com\ for\ more\ information).$ 

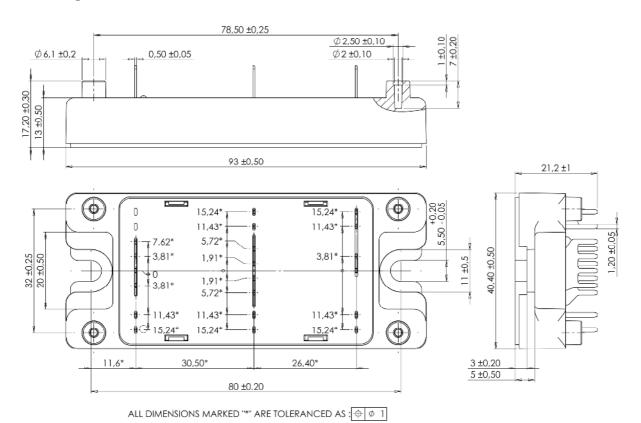
	Symbol	Characteristic	Min	Typ	Max	Unit
	R <sub>25</sub>	Resistance @ 25°C		50		kΩ
Ī	B 25/85	$T_{25} = 298.15 \text{ K}$		3952		K

$$R_T = \frac{R_{25}}{\exp \left[ B_{25/85} \left( \frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
$R_{thJC}$	Junction to Case Thermal Resistance		IGBT			0.18	°C/W
TthJC			Diode			0.34	C/ VV
$V_{ISOL}$	RMS Isolation Voltage, any terminal to case t	=1 min, 50/60Hz		4000			V
$T_{J}$	Operating junction temperature range		-40		150		
$T_{STG}$	Storage Temperature Range		-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		125	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight				160	g	

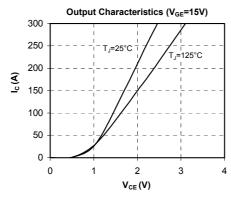
### SP4 Package outline (dimensions in mm)

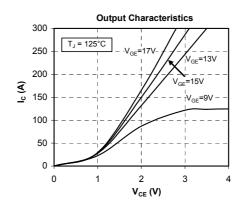


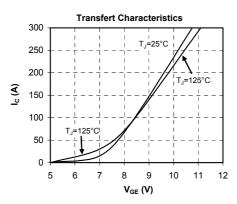
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

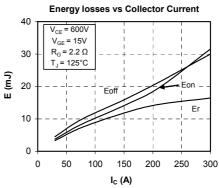


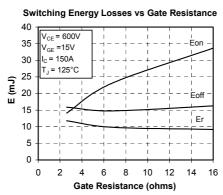
## **Typical Performance Curve**

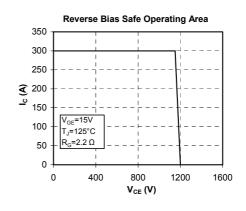


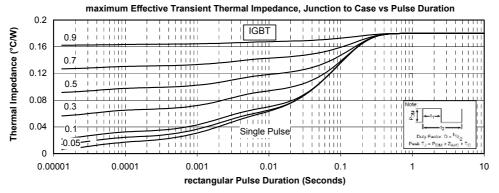




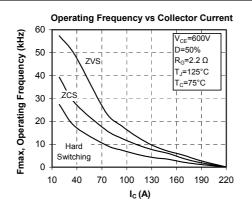


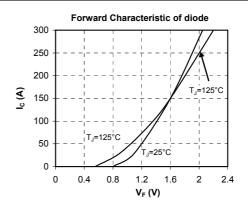


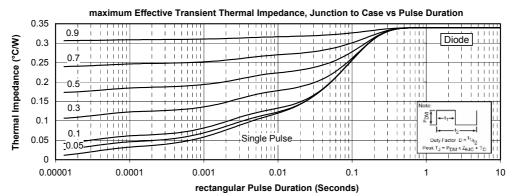












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